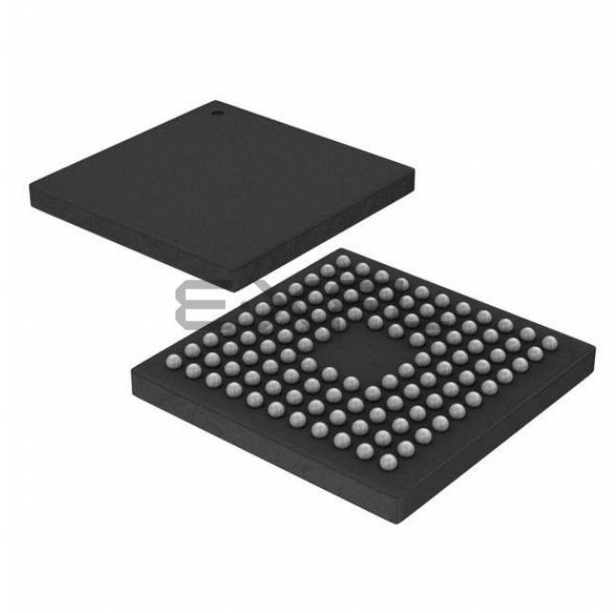

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	86
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg990f128-bga112t

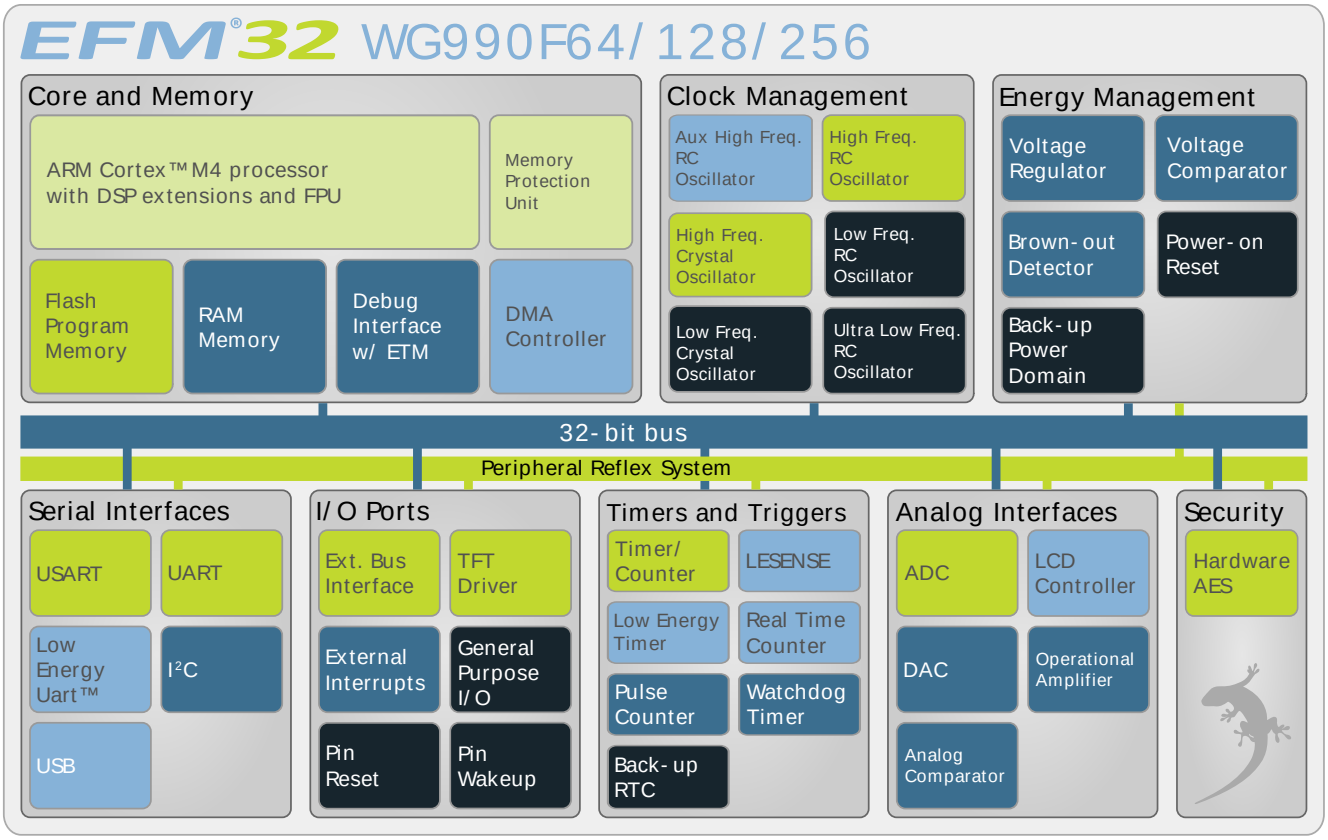
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M4, with DSP instruction support and floating-point unit, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32WG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32WG990 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32WG Reference Manual*.

A block diagram of the EFM32WG990 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M4 Core

The ARM Cortex-M4 includes a 32-bit RISC processor, with DSP instruction support and floating-point unit, which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M4 is described in detail in *ARM Cortex-M4 Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

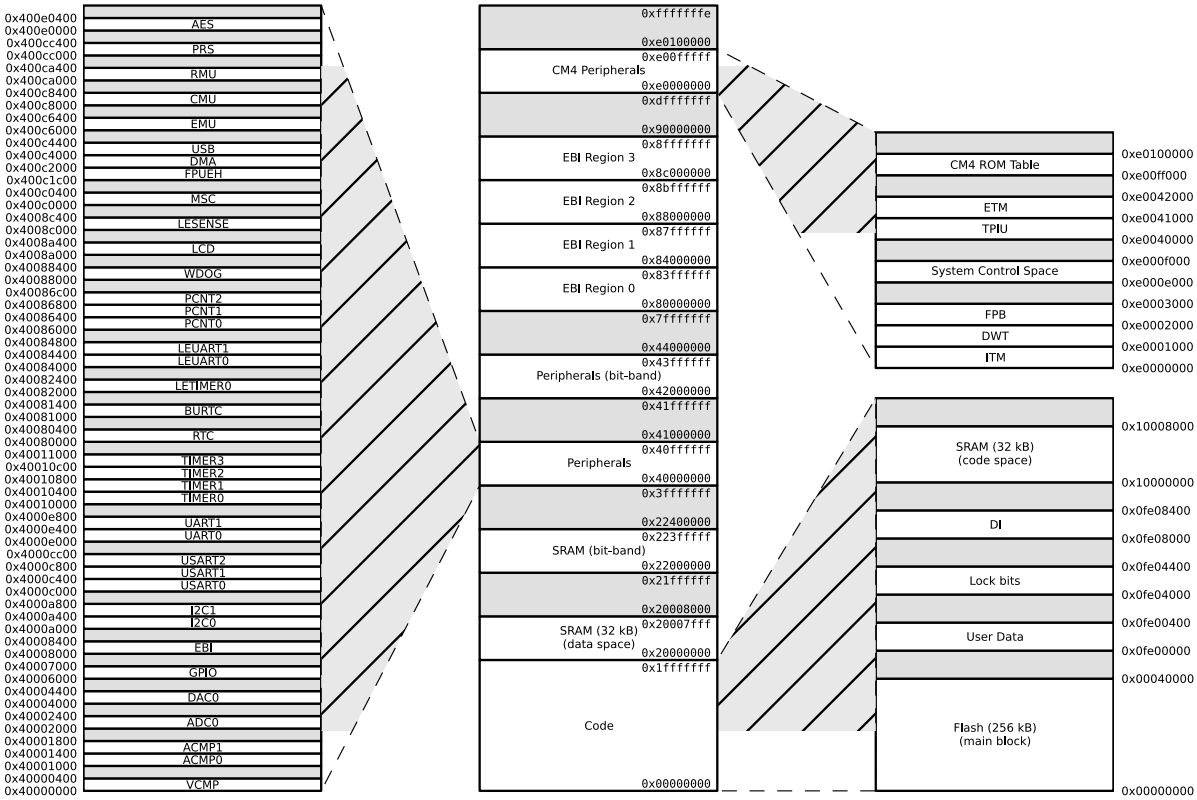
This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

Module	Configuration	Pin Connections
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	86 pins	Available pins are shown in Table 4.3 (p. 70)
LCD	Full configuration	LCD_SEG[33:0], LCD_COM[7:0], LCD_BCAP_P, LCD_BCAP_N, LCD_BEXT

2.3 Memory Map

The *EFM32WG990* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32WG990 Memory Map with largest RAM and Flash sizes



Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		271	286	µA/MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		275		µA/MHz
I_{EM1}	EM1 current (Production test condition = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		63	75	µA/MHz
		48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		65	76	µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		64	75	µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		65	77	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		65	76	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		66	78	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		67	79	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		68	82	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		68	81	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		70	83	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		74	87	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		76	89	µA/MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		106	120	µA/MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		112	129	µA/MHz
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=25°C		0.95[1]	1.7[1]	µA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		3.0[1]	4.0[1]	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.65	1.3	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		2.65	4.0	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.055	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.44	0.9	µA

[1]Using backup RTC.

3.4.1 EM1 Current Consumption

Figure 3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz

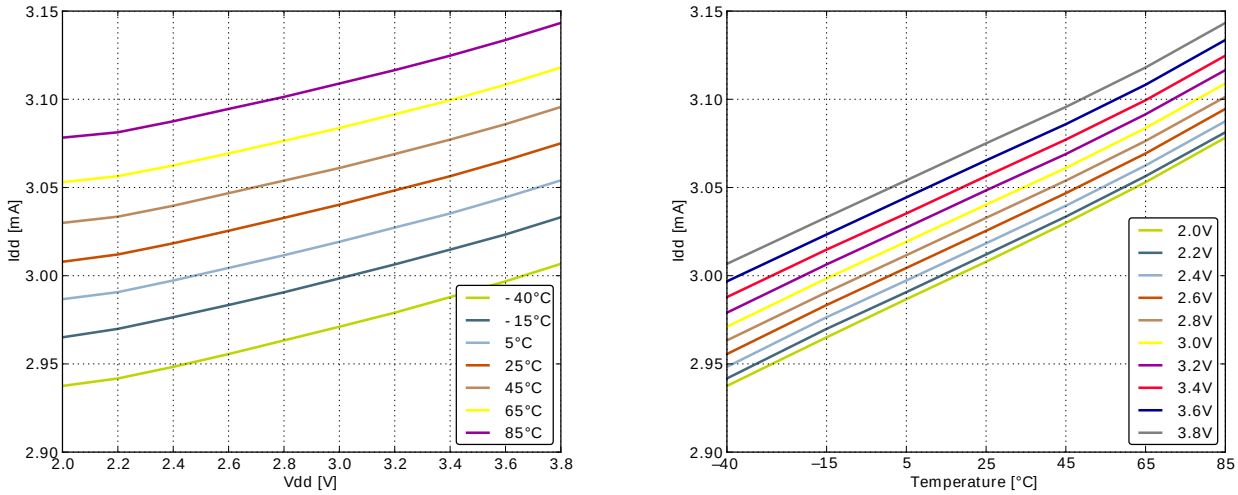
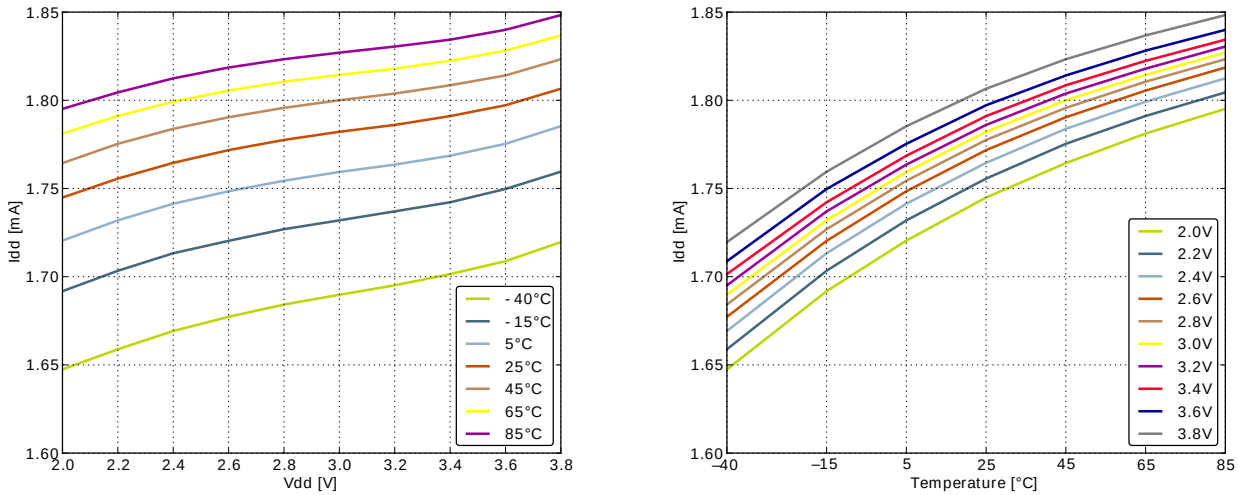


Figure 3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz



3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{PERASE}	Page erase time		20	20.4	20.8	ms
t_{DERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

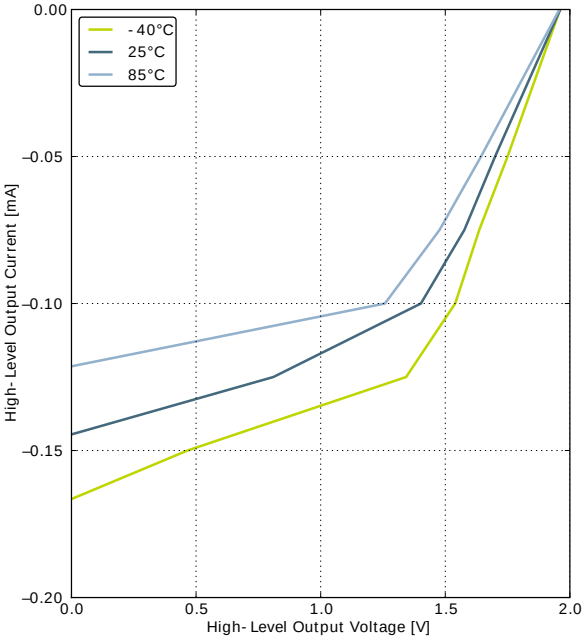
[1]Measured at 25°C

3.8 General Purpose Input Output

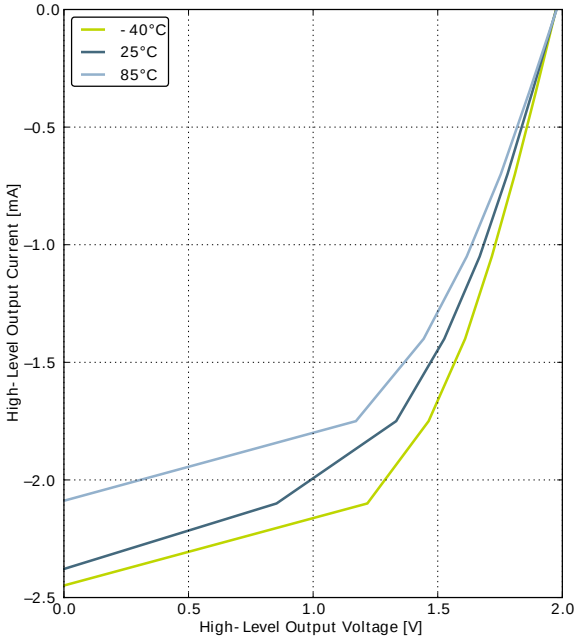
Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V

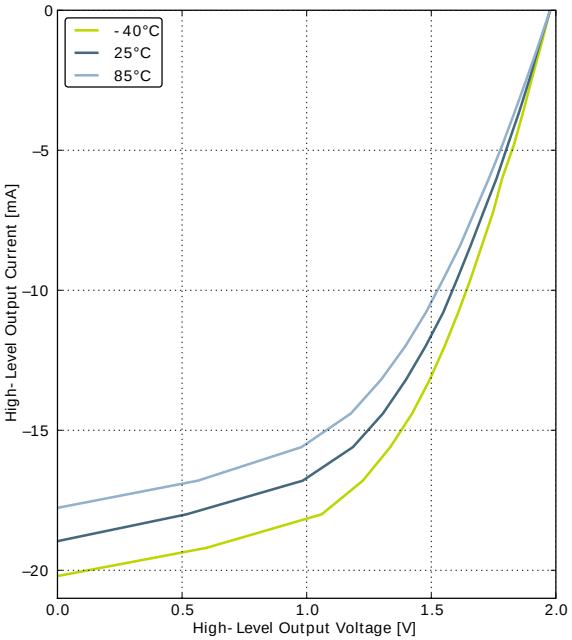
Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage



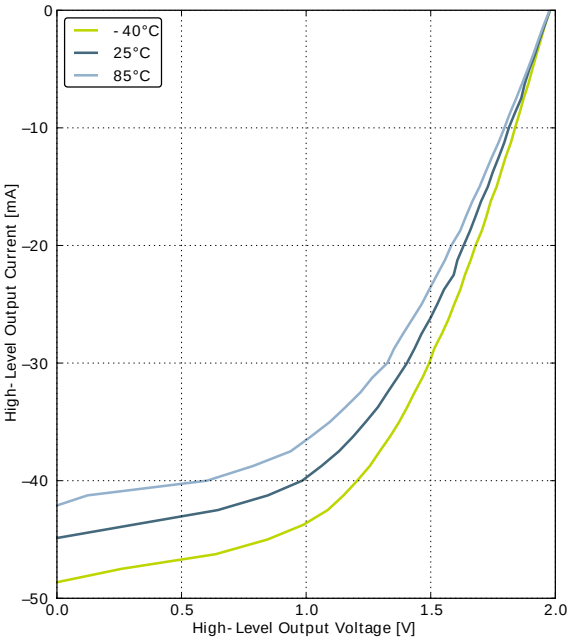
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

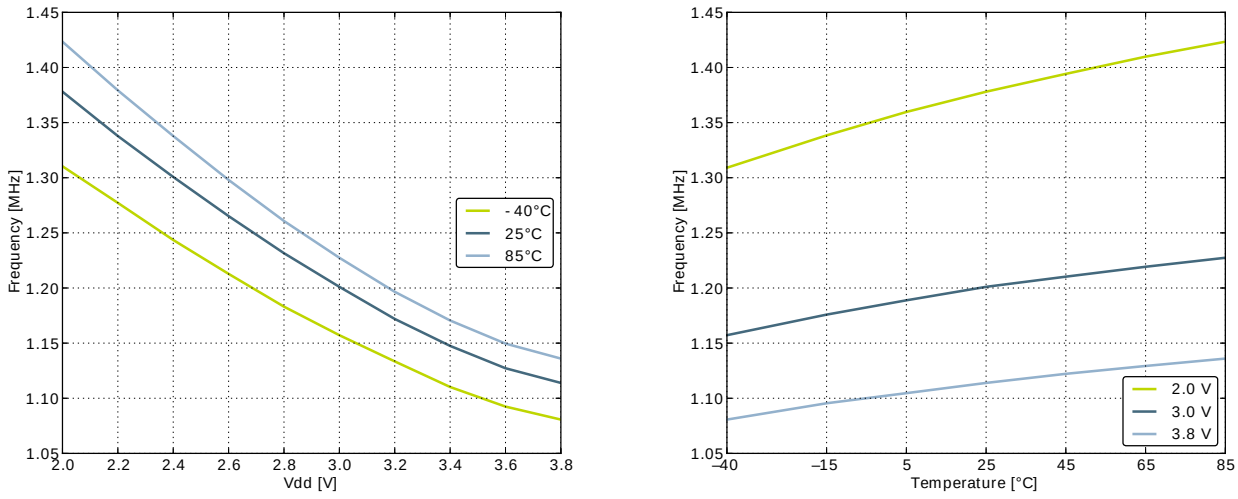
3.9.4 HFRCO

Table 3.12. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{HFRCO\_settling}$	Settling time after start-up	f_{HFRCO} = 14 MHz		0.6		Cycles
I_{HFRCO}	Current consumption	f_{HFRCO} = 28 MHz		165	215	µA
		f_{HFRCO} = 21 MHz		134	175	µA
		f_{HFRCO} = 14 MHz		106	140	µA
		f_{HFRCO} = 11 MHz		94	125	µA
		f_{HFRCO} = 6.6 MHz		77	105	µA
		f_{HFRCO} = 1.2 MHz		25	40	µA
DC_{HFRCO}	Duty cycle	f_{HFRCO} = 14 MHz	48.5	50	51	%
$TUNESTEP_{H-FRCO}$	Frequency step for LSB change in TUNING value			0.3[1]		%

[1]The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.18. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		79		dBc
$V_{ADCOFFSET}$	Offset voltage	After calibration, single ended	-3.5	0.3	3	mV
		After calibration, differential		0.3		mV
$TGRAD_{ADCTH}$	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL_{ADC}	Differential non-linearity (DNL)		-1	±0.7	4	LSB
INL_{ADC}	Integral non-linearity (INL), End point method			±1.2	±3	LSB
MC_{ADC}	No missing codes		11.999[1]	12		bits
$GAIN_{ED}$	Gain error drift	1.25V reference		0.01[2]	0.033[3]	%/°C
		2.5V reference		0.01[2]	0.03[3]	%/°C
$OFFSET_{ED}$	Offset error drift	1.25V reference		0.2[2]	0.7[3]	LSB/°C
		2.5V reference		0.2[2]	0.62[3]	LSB/°C

[1]On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

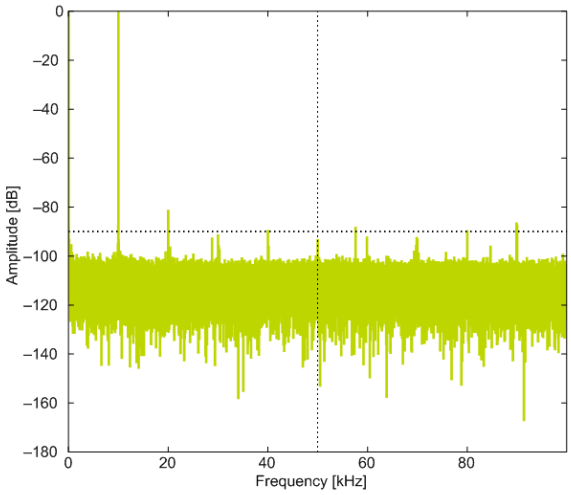
[2]Typical numbers given by abs(Mean) / (85 - 25).

[3]Max number given by (abs(Mean) + 3x stddev) / (85 - 25).

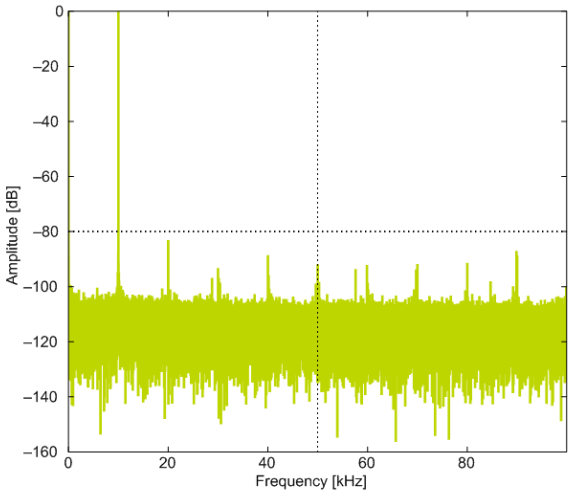
The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.24 (p. 37) and Figure 3.25 (p. 37) , respectively.

3.10.1 Typical performance

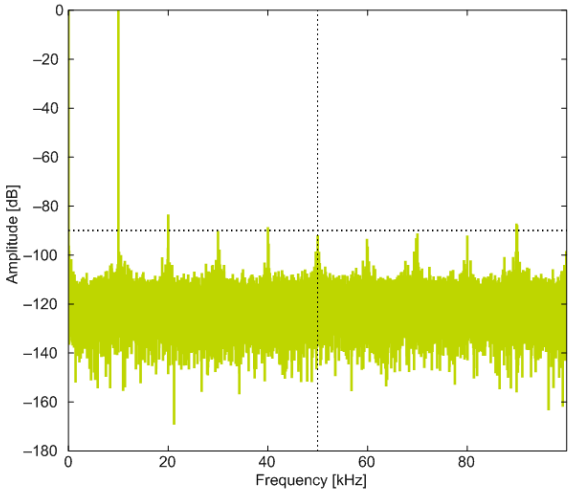
Figure 3.26. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



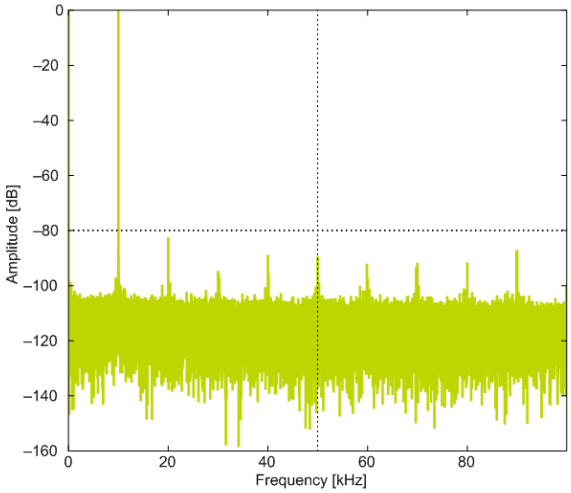
1.25V Reference



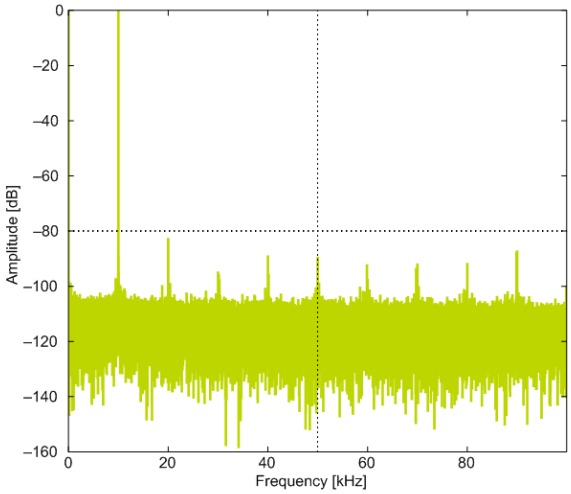
2.5V Reference



2XVDDVSS Reference

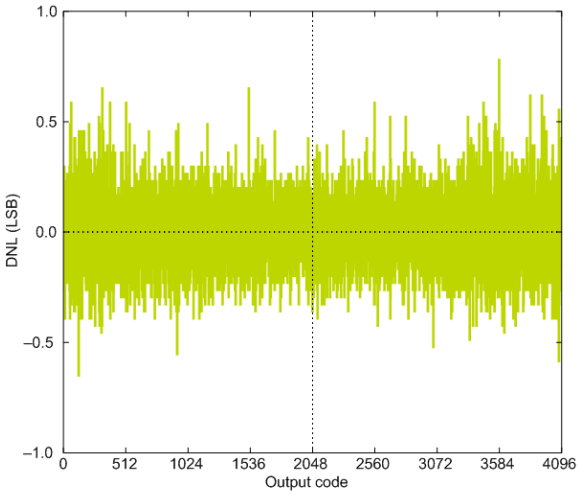


5VDIFF Reference

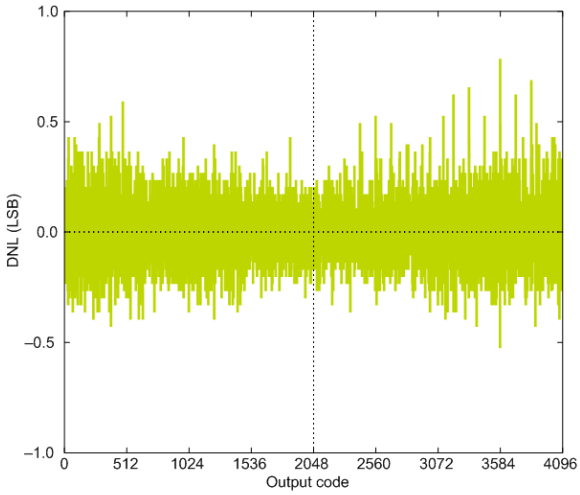


VDD Reference

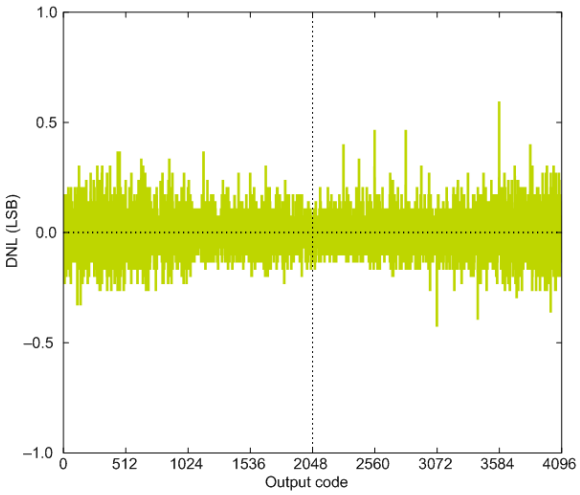
Figure 3.28. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C



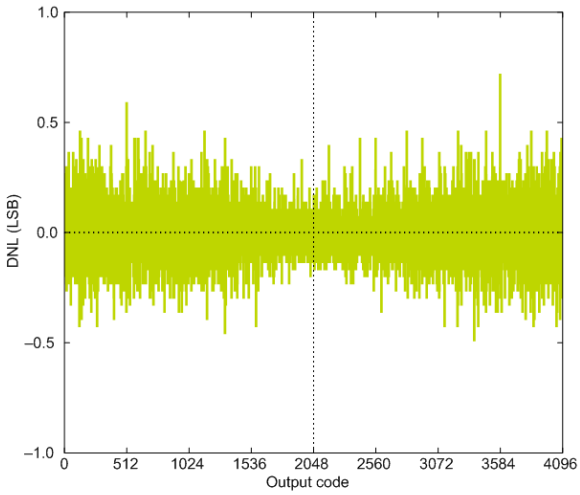
1.25V Reference



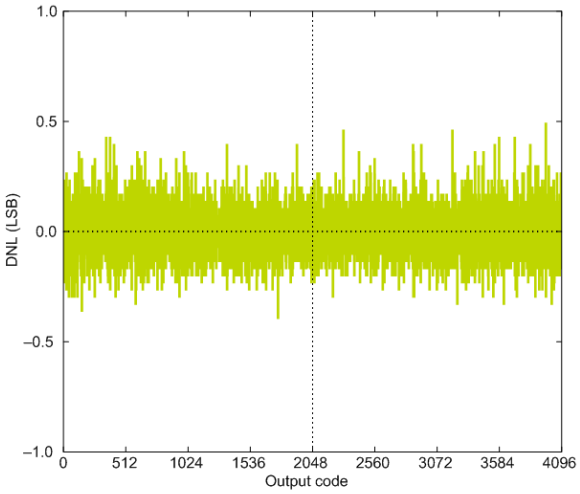
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	µA
G_{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW_{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM_{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C_L=75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C_L=75 pF		58		°
R_{INPUT}	Input Resistance			100		Mohm
R_{LOAD}	Load Resistance		200			Ohm
I_{LOAD_DC}	DC Load Current				11	mA
V_{INPUT}	Input Voltage	OPAxHCMDIS=0	V_{SS}		V_{DD}	V
		OPAxHCMDIS=1	V_{SS}		V_{DD}-1.2	V
V_{OUTPUT}	Output Voltage		V_{SS}		V_{DD}	V
V_{OFFSET}	Input Offset Voltage	Unity Gain, V_{SS}<V_{in}<V_{DD}, OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V_{SS}<V_{in}<$_{DD}$-1.2, OPAxHCMDIS=1		1		mV
V_{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR_{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/µs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/µs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		$µV_{RMS}$
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		$µV_{RMS}$

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		196		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		2590		μV_{RMS}

Figure 3.32. OPAMP Common Mode Rejection Ratio

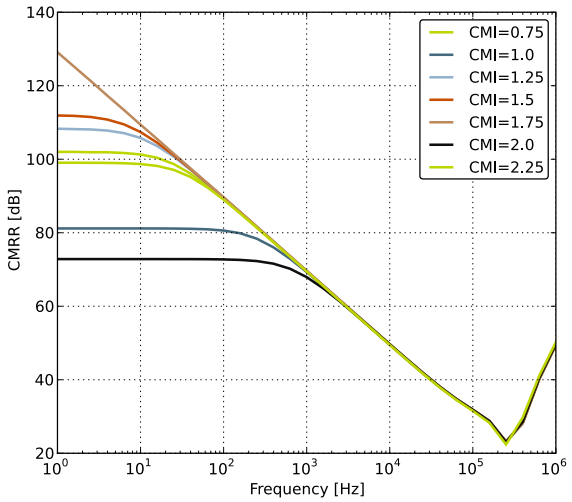
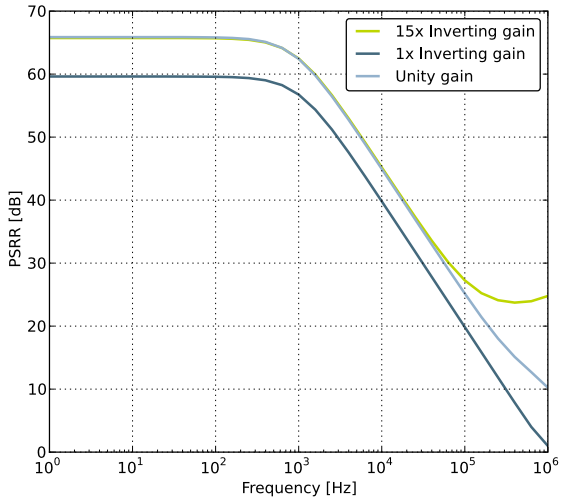


Figure 3.33. OPAMP Positive Power Supply Rejection Ratio



3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULLBIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	µA
		BIASPROG=0b1111, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	µA
		BIASPROG=0b1111, FULLBIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	µA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		µA
		Internal voltage reference		5		µA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	µs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 47) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

Table 3.20. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_WEn} [1 2 3 4]	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-6.00 + (WRHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_WEn} [1 2 3 4 5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	-14.00 + (WRSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_WEn} [1 2 3 4 5]	EBI_WEn/EBI_NANDWEn pulse width	-7.00 + ((WRSTRB +1) * $t_{HFCORECLK}$)			ns

[1]Applies for all addressing modes (figure only shows D16 addressing mode)
[2]Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by 1/2 * $t_{HFCLKNODIV}$.

Figure 3.39. EBI Address Latch Enable Related Output Timing

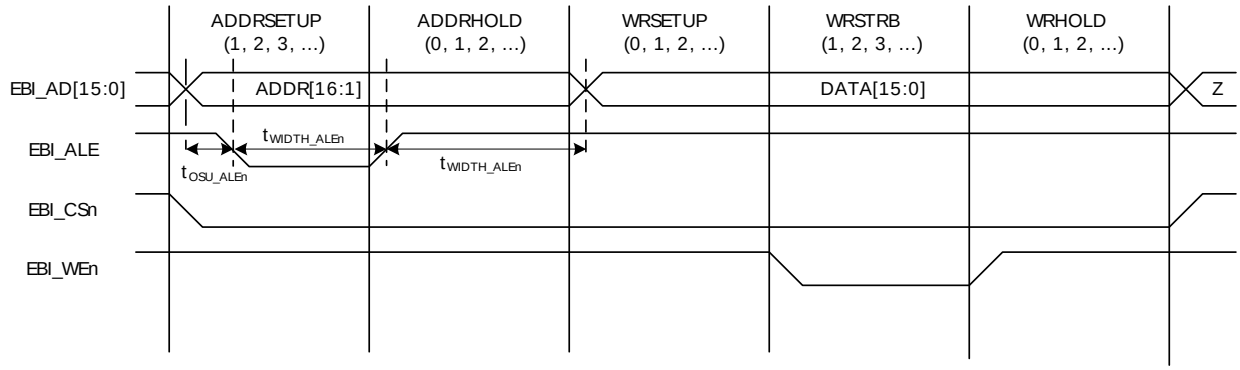


Table 3.21. EBI Address Latch Enable Related Output Timing

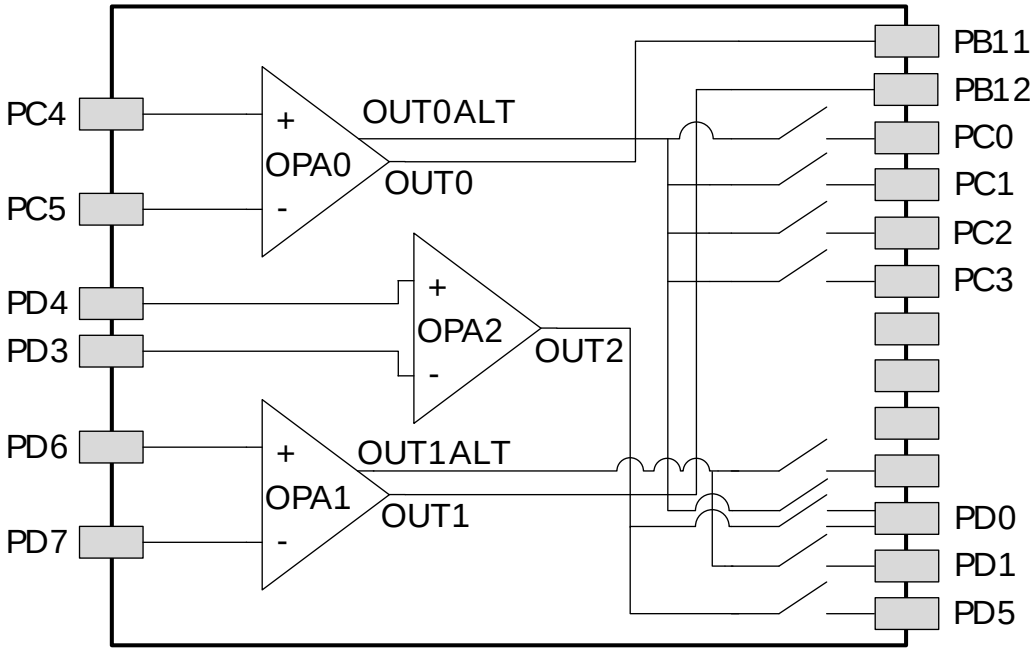
Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_ALEn} [1 2 3 4]	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	-6.00 + (ADDRHOLD[5] * $t_{HFCORECLK}$)			ns
t_{OSU_ALEn} [1 2 4]	Output setup time, from EBI_AD valid to leading EBI_ALE edge	-13.00 + (0 * $t_{HFCORECLK}$)			ns
t_{WIDTH_ALEn} [1 2 3 4]	EBI_ALEn pulse width	-7.00 + (ADDRSETUP+1) * $t_{HFCORECLK}$)			ns

[1]Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)
[2]Applies for all polarities (figure only shows active low signals)
[3] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of tOH_ALEn by $t_{HFCORECLK}$ - 1/2 * $t_{HFCLKNODIV}$.
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)
[5]Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
D4	VSS	Ground				
D5	IOVDD_6	Digital IO power supply 6.				
D6	PD9	LCD_SEG28	EBI_CS0 #0/1/2			
D7	IOVDD_5	Digital IO power supply 5.				
D8	PF1			TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
D9	PE7	LCD_COM3	EBI_A14 #0/1/2		US0_TX #1	
D10	PC8	ACMP1_CH0	EBI_A15 #0/1/2	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
D11	PC9	ACMP1_CH1	EBI_A09 #1/2	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
E1	PA6	LCD_SEG19	EBI_AD15 #0/1/2		LEU1_RX #1	ETM_TCLK #3 GPIO_EM4WU1
E2	PA5	LCD_SEG18	EBI_AD14 #0/1/2	TIM0_CDTI2 #0	LEU1_TX #1	LES_ALTEX4 #0 ETM_TD3 #3
E3	PA4	LCD_SEG17	EBI_AD13 #0/1/2	TIM0_CDTI1 #0	U0_RX #2	LES_ALTEX3 #0 ETM_TD2 #3
E4	PB0	LCD_SEG32	EBI_A16 #0/1/2	TIM1_CC0 #2		
E8	PF0			TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1/2/3
E9	PE0		EBI_A07 #0/1/2	TIM3_CC0 #1 PCNT0_S0IN #1	U0_TX #1 I2C1_SDA #2	
E10	PE1		EBI_A08 #0/1/2	TIM3_CC1 #1 PCNT0_S1IN #1	U0_RX #1 I2C1_SCL #2	
E11	PE3	BU_STAT	EBI_A10 #0		U1_RX #3	ACMP1_O #1
F1	PB1	LCD_SEG33	EBI_A17 #0/1/2	TIM1_CC1 #2		
F2	PB2	LCD_SEG34	EBI_A18 #0/1/2	TIM1_CC2 #2		
F3	PB3	LCD_SEG20/ LCD_COM4	EBI_A19 #0/1/2	PCNT1_S0IN #1	US2_TX #1	
F4	PB4	LCD_SEG21/ LCD_COM5	EBI_A20 #0/1/2	PCNT1_S1IN #1	US2_RX #1	
F8	VDD_DREG	Power supply for on-chip voltage regulator.				
F9	VSS_DREG	Ground for on-chip voltage regulator.				
F10	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1
F11	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size $C_{DECOUPLE}$ is required at this pin.				
G1	PB5	LCD_SEG22/ LCD_COM6	EBI_A21 #0/1/2		US2_CLK #1	
G2	PB6	LCD_SEG23/ LCD_COM7	EBI_A22 #0/1/2		US2_CS #1	
G3	VSS	Ground				
G4	IOVDD_0	Digital IO power supply 0.				
G8	IOVDD_4	Digital IO power supply 4.				
G9	VSS	Ground				
G10	PC6	ACMP0_CH6	EBI_A05 #0/1/2		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2
G11	PC7	ACMP0_CH7	EBI_A06 #0/1/2		LEU1_RX #0	LES_CH7 #0

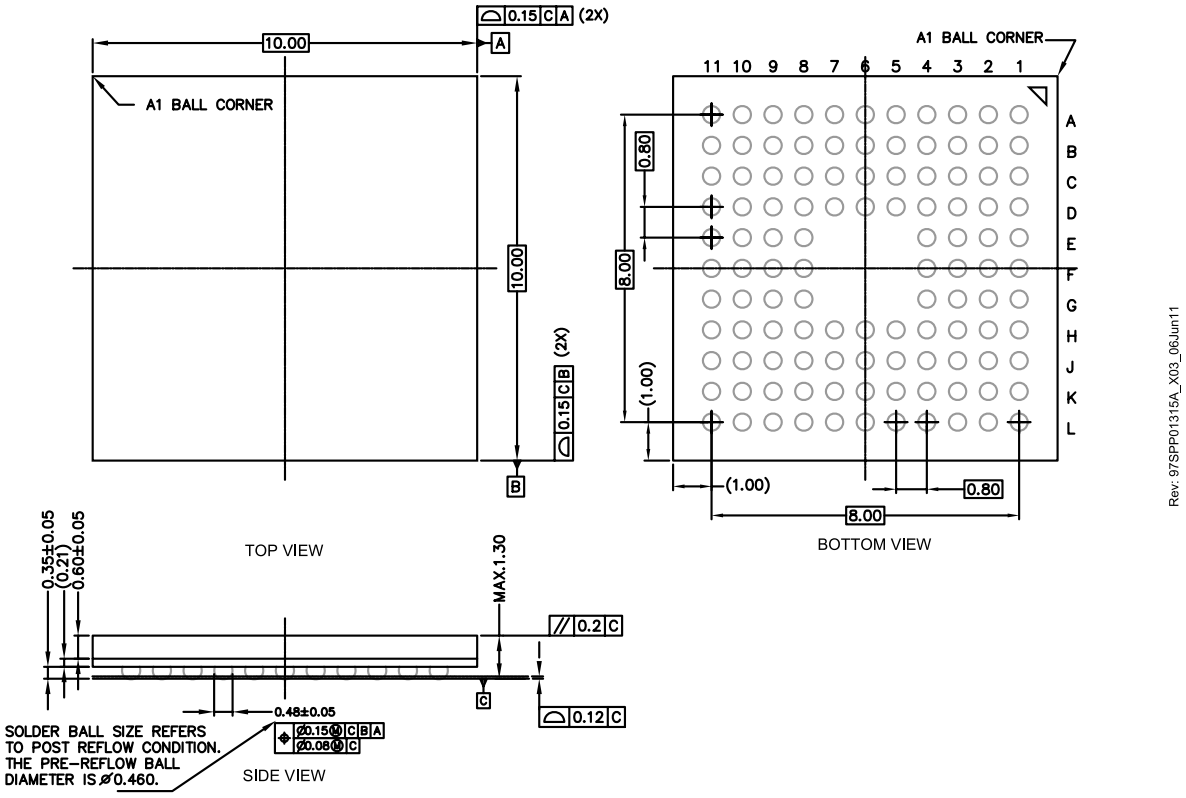
BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
					I2C0_SCL #2	ETM_TD0 #2
H1	PC0	ACMP0_CH0 DAC0_OUT0ALT #0/ OPAMP_OUT0ALT	EBI_A23 #0/1/2	TIM0_CC1 #4 PCNT0_S0IN #2	US0_TX #5 US1_TX #0 I2C0_SDA #4	LES_CH0 #0 PRS_CH2 #0
H2	PC2	ACMP0_CH2 DAC0_OUT0ALT #2/ OPAMP_OUT0ALT	EBI_A25 #0/1/2	TIM0_CDTI0 #4	US2_TX #0	LES_CH2 #0
H3	PD14				I2C0_SDA #3	
H4	PA7	LCD_SEG35	EBI_CSTFT #0/1/2			
H5	PA8	LCD_SEG36	EBI_DCLK #0/1/2	TIM2_CC0 #0		
H6	VSS	Ground				
H7	IOVDD_3	Digital IO power supply 3.				
H8	PD8	BU_VIN				CMU_CLK1 #1
H9	PD5	ADC0_CH5 OPAMP_OUT2 #0			LEU0_RX #0	ETM_TD3 #0/2
H10	PD6	ADC0_CH6 DAC0_P1 / OPAMP_P1		TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2 ETM_TD0 #0
H11	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1		TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
J1	PC1	ACMP0_CH1 DAC0_OUT0ALT #1/ OPAMP_OUT0ALT	EBI_A24 #0/1/2	TIM0_CC2 #4 PCNT0_S1IN #2	US0_RX #5 US1_RX #0 I2C0_SCL #4	LES_CH1 #0 PRS_CH3 #0
J2	PC3	ACMP0_CH3 DAC0_OUT0ALT #3/ OPAMP_OUT0ALT	EBI_NANDREn #0/1/2	TIM0_CDTI1 #4	US2_RX #0	LES_CH3 #0
J3	PD15				I2C0_SCL #3	
J4	PA12	LCD_BCAP_P	EBI_A00 #0/1/2	TIM2_CC0 #1		
J5	PA9	LCD_SEG37	EBI_DTEN #0/1/2	TIM2_CC1 #0		
J6	PA10	LCD_SEG38	EBI_VSNC #0/1/2	TIM2_CC2 #0		
J7	PB9		EBI_A03 #0/1/2		U1_TX #2	
J8	PB10		EBI_A04 #0/1/2		U1_RX #2	
J9	PD2	ADC0_CH2	EBI_A27 #0/1/2	TIM0_CC1 #3	USB_DMPU #0 US1_CLK #1	DBG_SWO #3
J10	PD3	ADC0_CH3 OPAMP_N2		TIM0_CC2 #3	US1_CS #1	ETM_TD1 #0/2
J11	PD4	ADC0_CH4 OPAMP_P2			LEU0_TX #0	ETM_TD2 #0/2
K1	PB7	LFXTAL_P		TIM1_CC0 #3	US0_TX #4 US1_CLK #0	
K2	PC4	ACMP0_CH4 DAC0_P0 / OPAMP_P0	EBI_A26 #0/1/2	TIM0_CDTI2 #4 LETIM0_OUT0 #3 PCNT1_S0IN #0	US2_CLK #0 I2C1_SDA #0	LES_CH4 #0
K3	PA13	LCD_BCAP_N	EBI_A01 #0/1/2	TIM2_CC1 #1		
K4	VSS	Ground				
K5	PA11	LCD_SEG39	EBI_HSNC #0/1/2			
K6	RESETn	Reset input, active low.				

Figure 4.2. Opamp Pinout



4.5 BGA112 Package

Figure 4.3. BGA112



Note:

1. The dimensions in parenthesis are reference.
2. Datum 'C' and seating plane are defined by the crown of the solder balls.
3. All dimensions are in millimeters.

Figure 5.2. BGA112 PCB Solder Mask

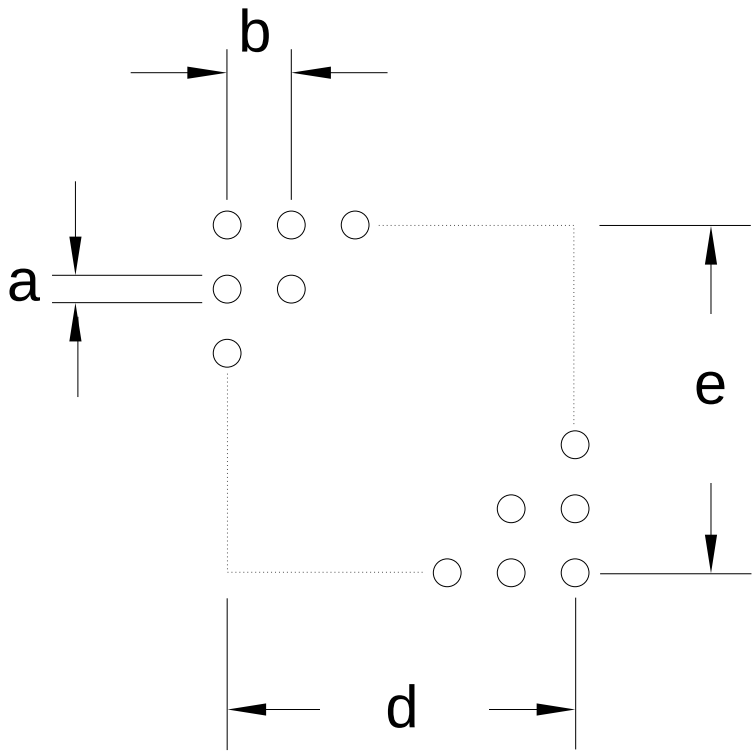


Table 5.2. BGA112 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.48
b	0.80
d	8.00
e	8.00

Table of Contents

List of Tables